

Nizami Gasanly

List of Publications by Year in descending order

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189
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#	ARTICLE	IF	CITATIONS
1	Optical phonons and structure of TlGaS_2 , TlGaSe_2 , and TlInS_2 layer single crystals. <i>Physica Status Solidi (B): Basic Research</i> , 1983, 116, 427-443.	1.5	57
2	Infrared and Raman Spectra of Layer InSe Single Crystals. <i>Physica Status Solidi (B): Basic Research</i> , 1978, 89, K43.	1.5	53
3	Donor-acceptor pair recombination in gallium sulfide. <i>Journal of Applied Physics</i> , 2000, 88, 7144-7149.	2.5	53
4	Raman scattering in some III-VI layer single crystals. <i>Physica Status Solidi (B): Basic Research</i> , 1978, 85, 381-386.	1.5	51
5	Donor-acceptor pair recombination in AgIn_5S_8 single crystals. <i>Journal of Applied Physics</i> , 1999, 85, 3198-3201.	2.5	45
6	Temperature dependence of the first-order Raman scattering in GaS layered crystals. <i>Solid State Communications</i> , 2000, 116, 147-151.	1.9	39
7	Vibrational Spectra of TlGaTe_2 , TlInTe_2 , and TlInSe_2 Layer Single Crystals. <i>Physica Status Solidi (B): Basic Research</i> , 1980, 97, 367-377.	1.5	38
8	Thermally stimulated current analysis of shallow levels in TlGaS_2 layered single crystals. <i>Semiconductor Science and Technology</i> , 2003, 18, 834-838.	2.0	38
9	Gd-doped ZnO nanoparticles: Synthesis, structural and thermoluminescence properties. <i>Journal of Luminescence</i> , 2019, 207, 220-225.	3.1	37
10	Structural and temperature-dependent optical properties of thermally evaporated CdS thin films. <i>Materials Science in Semiconductor Processing</i> , 2019, 93, 148-152.	4.0	37
11	Radiative donor-acceptor pair recombination in TlInS_2 single crystals. <i>Semiconductor Science and Technology</i> , 1999, 14, 599-603.	2.0	34
12	Raman study of layer TlGaS_2 , TlInS_2 , and TlGaSe_2 crystals. <i>Physica Status Solidi (B): Basic Research</i> , 1978, 86, K49.	1.5	33
13	Hall effect, space-charge limited current and photoconductivity measurements on TlGaSe_2 layered crystals. <i>Semiconductor Science and Technology</i> , 2004, 19, 505-509.	2.0	30
14	Vibrational Spectra of Spinel-Type Compound CuIn_5S_8 . <i>Physica Status Solidi (B): Basic Research</i> , 1992, 169, K115.	1.5	28
15	Photoelectronic and electrical properties of CuIn_5S_8 single crystals. <i>Crystal Research and Technology</i> , 2003, 38, 1063-1070.	1.3	28
16	Temperature dependence of the Raman-active phonon frequencies in indium sulfide. <i>Solid State Communications</i> , 1999, 110, 231-236.	1.9	27
17	Optical Properties of TlGaSeS Layered Single Crystals. <i>Journal of the Korean Physical Society</i> , 2007, 51, 2031.	0.7	27
18	Raman and Infrared Studies of AgIn_5S_8 and CuIn_5S_8 Single Crystals. <i>Physica Status Solidi (B): Basic Research</i> , 1993, 177, K31.	1.5	26

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19	Low-temperature visible photoluminescence spectra of TlGaSe ₂ layered crystal. Journal of Luminescence, 2000, 86, 39-43.	3.1	26
20	Electrical conductivity and Hall mobility in p-type TlGaSe ₂ crystals. Materials Research Bulletin, 2004, 39, 1351-1357.	5.2	25
21	Temperature-dependent Raman scattering spectra of μ -GaSe layered crystal. Materials Research Bulletin, 2002, 37, 169-176.	5.2	24
22	Coexistence of Indirect and Direct Optical Transitions, Refractive, Index and Oscillator Parameters in TlGaS ₂ , TlGaSe ₂ , and TlInS ₂ Layered Single Crystals. Journal of the Korean Physical Society, 2010, 57, 164-168.	0.7	24
23	Crystal Data, Electrical Resistivity and Mobility in Cu ₃ In ₅ Se ₉ and Cu ₃ In ₅ Te ₉ Single Crystals. Crystal Research and Technology, 1997, 32, 395-400.	1.3	23
24	Trapping center parameters of TlGaSe ₂ layered crystals. Physica B: Condensed Matter, 2004, 344, 249-254.	2.7	23
25	Vibrational Spectra of TlInS ₂ , TlIn _{0.95} Ga _{0.05} S ₂ , and TlIn(S _{0.8} Se _{0.2}) ₂ Crystals in the Vicinity of Phase Transitions. Physica Status Solidi (B): Basic Research, 1986, 137, 21-32.	1.5	22
26	Low-temperature photoluminescence spectra of layered semiconductor TlGaS ₂ . Solid State Communications, 1998, 105, 21-24.	1.9	22
27	Low-temperature photoluminescence spectra of InS single crystals. Solid State Communications, 1997, 101, 797-799.	1.9	21
28	Temperature- and excitation intensity-dependent photoluminescence in TlInSeS single crystals. Journal of Physics Condensed Matter, 2002, 14, 13685-13692.	1.8	21
29	Optoelectronic and electrical properties of TlGaS ₂ single crystal. Physica Status Solidi A, 2005, 202, 2501-2507.	1.7	21
30	Electron-phonon short-range interactions mobility and p- to n-type conversion in TlGaS ₂ crystals. Crystal Research and Technology, 2006, 41, 174-179.	1.3	21
31	Composition-tuned band gap energy and refractive index in Ga _x Se _{1-x} layered mixed crystals. Materials Chemistry and Physics, 2017, 190, 74-78.	4.0	21
32	Polymorphism of InS at high pressures. Solid State Communications, 1982, 44, 1383-1385.	1.9	20
33	Photoelectronic, optical and electrical properties of TlInS ₂ single crystals. Physica Status Solidi A, 2003, 199, 277-283.	1.7	20
34	Temperature effect on dark electrical conductivity, Hall coefficient, space charge limited current and photoconductivity of TlGaS ₂ single crystals. Semiconductor Science and Technology, 2005, 20, 446-452.	2.0	20
35	Temperature effects on the structural and optical properties of the TlInSe _{2-x} S ₂ (1-x) mixed crystals ($\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si1.gif" Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 107 T$) Journal of Alloys and Compounds, 2017, 724, 98-102.	5.5	20
36	Mixed one- and two-mode behaviour of optical phonons in TlGaS _{2-x} Se ₂ (1-x) and TlInS _{2-x} Se ₂ (1-x) layer solid solutions. Physica Status Solidi (B): Basic Research, 1979, 91, K1.	1.5	19

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37	Crystal Data, Photoconductivity and Carrier Scattering Mechanisms in CuIn ₅ S ₈ Single Crystals. Crystal Research and Technology, 2001, 36, 1399.	1.3	19
38	Spectroscopic ellipsometry study of above-band gap optical constants of layered structured TlGaSe ₂ , TlGaS ₂ and TlInS ₂ single crystals. Physica B: Condensed Matter, 2012, 407, 4193-4197.	2.7	19
39	Low-temperature phase transitions in TlGaS ₂ layer crystals. Solid State Communications, 1993, 88, 387-390.	1.9	18
40	Investigation of carrier scattering mechanisms in TlInS ₂ single crystals by Hall effect measurements. Crystal Research and Technology, 2004, 39, 439-447.	1.3	18
41	Design and Applications of Yb/Ga ₂ Se ₃ /C Schottky Barriers. IEEE Sensors Journal, 2017, 17, 4429-4434.	4.7	18
42	Temperature dependence of band gaps in sputtered SnSe thin films. Journal of Physics and Chemistry of Solids, 2019, 131, 22-26.	4.0	18
43	Synthesis and temperature-tuned band gap characteristics of magnetron sputtered ZnTe thin films. Physica B: Condensed Matter, 2020, 582, 411968.	2.7	18
44	Optical properties of TlInS ₂ layered single crystals near the absorption edge. Journal of Materials Science, 2006, 41, 3569-3572.	3.7	17
45	The effect of film thickness, Se/S ratio and annealing temperature on the nonlinear absorption behaviors in amorphous Ga _{1-x} Se _x (0 ≤ x ≤ 1) thin films. Optics Communications, 2013, 288, 107-113.	2.1	17
46	Temperature-dependent band gap characteristics of Bi ₁₂ SiO ₂₀ single crystals. Journal of Applied Physics, 2019, 126, .	2.5	17
47	Long-wavelength lattice vibrations of TlIn _{2-x} Se _{2(1-x)} and TlGaS _{2-x} Se _{2(1-x)} layer solid solutions. Physica Status Solidi (B): Basic Research, 1979, 95, K27.	1.5	16
48	Indirect nuclear exchange coupling and electronic structure of the chain semiconductor TlSe: A ²⁰³ Tl and ²⁰⁵ Tl NMR study. Physical Review B, 2001, 63, .	3.2	16
49	Trapping centers in undoped GaS layered single crystals. Applied Physics A: Materials Science and Processing, 2003, 77, 603-606.	2.3	16
50	Effect of temperature and isomorphic atom substitution on optical absorption edge of TlIn _{2-x} Se _{2(1-x)} mixed crystals (0.25 ≤ x ≤ 1). Crystal Research and Technology, 2010, 45, 525-528.	1.3	16
51	The nonlinear and saturable absorption characteristics of Ga _{0.90} In _{0.10} Se and Ga _{0.85} In _{0.15} Se semiconductor crystals and their amorphous thin films. Journal of Optics (United Kingdom), 2011, 13, 075203.	2.2	16
52	Traps distribution in sol-gel synthesized ZnO nanoparticles. Materials Letters, 2019, 245, 103-105.	2.6	16
53	Trap Distribution in TlInS ₂ Layered Crystals from Thermally Stimulated Current Measurements. Journal of the Korean Physical Society, 2008, 52, 367-373.	0.7	16
54	Optical Phonons in GaS _{1-x} Se _x Layer Mixed Crystals. Physica Status Solidi (B): Basic Research, 1983, 120, 137-147.	1.5	15

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55	Anisotropy of Electrical Resistivity and Hole Mobility in InTe Single Crystals. Crystal Research and Technology, 1996, 31, 673-678.	1.3	15
56	Investigation of Localized Levels in GaS _{0.5} Se _{0.5} Layered Crystals by Means of Electrical, Space-Charge Limited Current and Photoconductivity Measurements. Physica Status Solidi A, 2002, 194, 81-88.	1.7	15
57	Temperature dependence of Raman-active mode frequencies and linewidths in TlGaSe ₂ layered crystals. Crystal Research and Technology, 2005, 40, 264-270.	1.3	15
58	Anomalous heating rate dependence of thermoluminescence in Tl ₂ GaInS ₄ single crystals. Journal of Materials Science, 2014, 49, 8294-8300.	3.7	15
59	The effect of Ga/In ratio and annealing temperature on the nonlinear absorption behaviors in amorphous TlGa _x In _(1-x) S ₂ (0 ≤ x ≤ 1) chalcogenide thin films. Optics and Laser Technology, 2020, 128, 106230.	4.6	15
60	Deep Traps Distribution in TlInS ₂ Layered Crystals. Acta Physica Polonica A, 2009, 115, 732-737.	0.5	15
61	Pressure dependence of the Raman spectra of indium sulphide. Solid State Communications, 1981, 39, 587-589.	1.9	14
62	Raman Scattering in Pb(MoO ₄) _x (WO ₄) _{1-x} Mixed Crystals. Physica Status Solidi (B): Basic Research, 1982, 110, K21.	1.5	14
63	Raman Spectroscopy of Soft and Rigid Modes in Ferroelectric TlInS ₂ . Physica Status Solidi (B): Basic Research, 1989, 153, 727-739.	1.5	14
64	Thermally stimulated current measurements in as-grown TlGaSeS layered single crystals. Current Applied Physics, 2009, 9, 1278-1282.	2.4	14
65	Investigation of optical properties of Bi ₁₂ GeO ₂₀ sillenite crystals by spectroscopic ellipsometry and Raman spectroscopy. Ceramics International, 2020, 46, 12905-12910.	4.8	14
66	Low-temperature photoluminescence spectra of TlIn _x Ga _{1-x} S ₂ layer mixed crystals. Solid State Communications, 1995, 94, 777-782.	1.9	13
67	Dependence of the photoluminescence of Tl ₂ InGaS ₄ layered crystal on temperature and excitation intensity. Solid State Communications, 1998, 108, 525-530.	1.9	13
68	Anharmonic line shift and linewidth of the Raman modes in TlInS ₂ layered crystals. Journal of Raman Spectroscopy, 2004, 35, 55-60.	2.5	13
69	Light illumination effect on the electrical and photovoltaic properties of In ₆ S ₇ crystals. Journal of Physics Condensed Matter, 2006, 18, 4609-4614.	1.8	13
70	Refractive index, static dielectric constant, energy band gap and oscillator parameters of Ga ₂ SeS single crystals. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 3165-3169.	1.8	13
71	Defect assisted nonlinear absorption and optical limiting in amorphous TlGaS ₂ (1-x)Se ₂ (x) (0 ≤ x ≤ 1) thin films. Journal of Luminescence, 2022, 241, 118540.	3.1	13
72	Optical phonons in layer TlInSe ₂ single crystals. Physica Status Solidi (B): Basic Research, 1979, 92, K139.	1.5	12

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73	Effect of magnetic field and gamma irradiation on the electrical properties and structure of the Tl-based ceramic superconductors. <i>Superconductor Science and Technology</i> , 2000, 13, 161-164.	3.5	12
74	Trap levels in layered semiconductor Ga ₂ SeS. <i>Solid State Communications</i> , 2004, 132, 857-861.	1.9	12
75	Determination of trapping center parameters of Tl ₂ InGaS ₄ -layered crystals by thermally stimulated current measurements. <i>Journal of Alloys and Compounds</i> , 2006, 417, 23-28.	5.5	12
76	Raman scattering in TlInS ₂ xSe ₂ (1-x) layered mixed crystals (0.25 ≤ x ≤ 1): Compositional dependence of the mode frequencies and line widths. <i>Physica B: Condensed Matter</i> , 2011, 406, 3374-3376.	2.7	12
77	Elastic coefficients in TlGa(S _{1-x} Se) ₂ and TlIn _x Ga _{1-x} S ₂ layer mixed crystal by Brillouin scattering. <i>Physica B: Condensed Matter</i> , 1993, 192, 371-377.	2.7	11
78	Composition variations of lattice parameters of TlIn(S _{1-x} Se) ₂ , TlIn(S _{1-x} Se) ₂ , and TlIn _{1-x} Ga _x Se ₂ mixed crystals. <i>Crystal Research and Technology</i> , 1995, 30, 109-113.	1.3	11
79	TEMPERATURE-TUNED BAND GAP ENERGY AND OSCILLATOR PARAMETERS OF TlInSeS LAYERED SINGLE CRYSTALS. <i>International Journal of Modern Physics B</i> , 2008, 22, 3931-3939.	2.0	11
80	Structural and Optical Properties of Ga ₂ Se ₃ Crystals by Spectroscopic Ellipsometry. <i>Journal of Electronic Materials</i> , 2019, 48, 2418-2422.	2.2	11
81	Temperature-dependent optical characteristics of sputtered NiO thin films. <i>Applied Physics A: Materials Science and Processing</i> , 2022, 128, 1.	2.3	11
82	Photoluminescence of layered Ga _{1-x} In _x Se crystals at two-photon optical excitation. <i>Physica Status Solidi A</i> , 1978, 47, K157-K160.	1.7	10
83	Structural and Electrical Characterization of Ag ₃ Ga ₅ Te ₉ and Ag ₃ In ₅ Se ₉ Crystals. <i>Crystal Research and Technology</i> , 1998, 33, 923-928.	1.3	10
84	Carrier Transport Properties of InS Single Crystals. <i>Crystal Research and Technology</i> , 2002, 37, 1104-1112.	1.3	10
85	Infrared photoluminescence from TlGaS ₂ layered single crystals. <i>Crystal Research and Technology</i> , 2004, 39, 800-806.	1.3	10
86	Thermally stimulated currents in layered semiconductor Tl ₄ In ₃ GaS ₈ . <i>Semiconductor Science and Technology</i> , 2006, 21, 1250-1255.	2.0	10
87	Specific features of the optical spectra in Tl ₂ In ₂ S ₃ Se layered single crystals. <i>Crystal Research and Technology</i> , 2007, 42, 621-625.	1.3	10
88	Temperature- and excitation-dependent photoluminescence in TlGaSeS layered crystals. <i>Journal of Alloys and Compounds</i> , 2011, 509, 4205-4208.	5.5	10
89	Effect of lithium doping on the properties of Tl-based superconductors. <i>Superconductor Science and Technology</i> , 2001, 14, 738-740.	3.5	9
90	Effect of B ₂ O ₃ addition on the formation and properties of Tl-2212 and Tl-2223 superconductors. <i>Physica Status Solidi A</i> , 2003, 199, 272-276.	1.7	9

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91	Dispersive optical constants and temperature tuned band gap energy of $\text{Tl}_2\text{InGa}_4\text{S}_4$ layered crystals. <i>Journal of Physics Condensed Matter</i> , 2007, 19, 256210.	1.8	9
92	Thermally assisted variable range hopping in $\text{Tl}_4\text{S}_3\text{Se}$ crystal. <i>Bulletin of Materials Science</i> , 2015, 38, 593-598.	1.7	9
93	Ellipsometry study of optical parameters of AgIn_5S_8 crystals. <i>Physica B: Condensed Matter</i> , 2015, 478, 127-130.	2.7	9
94	Longâ€Wave Optical Phonons in In_6S_7 Layer Crystals. <i>Physica Status Solidi (B): Basic Research</i> , 1981, 106, K47.	1.5	8
95	Infrared Reflectivity Spectra of $\text{Cu}_3\text{In}_5\text{S}_9$ Layer Single Crystals. <i>Physica Status Solidi (B): Basic Research</i> , 1987, 144, K73.	1.5	8
96	Voltage-current characteristics of the thallium-based ceramic superconductors. <i>Superconductor Science and Technology</i> , 1999, 12, 592-596.	3.5	8
97	Electrical and photoconductive properties of $\text{GaS}_{0.75}\text{Se}_{0.25}$ mixed crystals. <i>Crystal Research and Technology</i> , 2005, 40, 253-258.	1.3	8
98	Analysis of the Hall effect in TlGaTe_2 single crystals. <i>Journal of Physics Condensed Matter</i> , 2009, 21, 235802.	1.8	8
99	Temperatureâ€tuned band gap energy and oscillator parameters of $\text{Tl}_2\text{InGaSe}_4$ semiconducting layered single crystals. <i>Crystal Research and Technology</i> , 2009, 44, 322-326.	1.3	8
100	DETERMINATION OF TRAPPING CENTER PARAMETERS OF $\text{Tl}_2\text{Ga}_2\text{S}_3\text{Se}$ LAYERED CRYSTALS BY THERMALLY STIMULATED CURRENT MEASUREMENTS. <i>International Journal of Modern Physics B</i> , 2010, 24, 2149-2161.	2.0	8
101	Effect of temperature on band gap of PbWO_4 single crystals grown by Czochralski method. <i>Physica Scripta</i> , 2022, 97, 045803.	2.5	8
102	Infrared spectra of the layer compound InS . <i>Physica Status Solidi (B): Basic Research</i> , 1979, 95, K89.	1.5	7
103	Vibrational Spectra of a GaTe Layer Crystal. <i>Physica Status Solidi (B): Basic Research</i> , 1980, 100, K53.	1.5	7
104	Lattice Vibrations in CuIn_5S_8 Crystals. <i>Physica Status Solidi (B): Basic Research</i> , 1990, 158, K1.	1.5	7
105	Low-Temperature Raman Scattering Spectra of $\text{GaS}_x\text{S}_{1-x}$ Layered Mixed Crystals. <i>Crystal Research and Technology</i> , 2002, 37, 1011-1017.	1.3	7
106	Thermally stimulated currents in layered Ga_4Se_3 semiconductor. <i>Physica Status Solidi A</i> , 2004, 201, 2980-2985.	1.7	7
107	Compositional dependence of the Raman lineshapes in $\text{GaS}_x\text{Se}_{1-x}$ layered mixed crystals. <i>Journal of Raman Spectroscopy</i> , 2005, 36, 879-883.	2.5	7
108	Excitation intensity and temperature-dependent photoluminescence and optical absorption in $\text{Tl}_4\text{Ga}_3\text{InSe}_8$ layered crystals. <i>Crystal Research and Technology</i> , 2006, 41, 822-828.	1.3	7

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109	Temperature- and photo-excitation effects on the electrical properties of $\text{Tl}_{4-x}\text{Se}_{3-x}\text{S}$ crystals. <i>Journal of Physics Condensed Matter</i> , 2009, 21, 115801.	1.8	7
110	Shallow trapping center parameters in as-grown AgIn_5S_8 crystals determined by thermally stimulated current measurements. <i>Crystal Research and Technology</i> , 2009, 44, 1267-1271.	1.3	7
111	Determination of optical parameters of $\text{Ga}_{0.75}\text{In}_{0.25}\text{Se}$ layered crystals. <i>Crystal Research and Technology</i> , 2012, 47, 530-534.	1.3	7
112	Energy Band Diagram and Current Transport Mechanism In $\text{p-MgO/n-Ga}_4\text{Se}_3\text{S}$. <i>IEEE Transactions on Electron Devices</i> , 2015, 62, 102-106.	3.0	7
113	Temperature-dependent optical properties of GaSe layered single crystals. <i>Philosophical Magazine</i> , 2016, 96, 2564-2573.	1.6	7
114	Ellipsometric study of optical properties of $\text{GaS}_x\text{Se}_{1-x}$ layered mixed crystals. <i>Optical Materials</i> , 2016, 54, 155-159.	3.6	7
115	Thermoluminescence properties of ZnO nanoparticles in the temperature range $10\text{--}300\text{K}$. <i>Journal of Sol-Gel Science and Technology</i> , 2016, 78, 76-81.	2.4	7
116	Spectroscopic ellipsometry study of $\text{Bi}_{12}\text{TiO}_{20}$ single crystals. <i>Journal of Materials Science: Materials in Electronics</i> , 2021, 32, 7019-7025.	2.2	7
117	Infrared Reflection Spectra of Cu_3BC Single Crystals. <i>Physica Status Solidi (B): Basic Research</i> , 1990, 158, K85.	1.5	6
118	Anharmonicity of Zone-Center Optical Phonons: Raman Scattering Spectra of $\text{GaSe}_{0.5}\text{S}_{0.5}$ Layered Crystal. <i>Physica Scripta</i> , 2002, 65, 534-538.	2.5	6
119	Below and above bandgap excited photoluminescence in $\text{Tl}_4\text{InGa}_3\text{S}_8$ layered single crystals. <i>Journal of Physics Condensed Matter</i> , 2007, 19, 456221.	1.8	6
120	Effect of isomorphic atom substitution on the refractive index and oscillator parameters of $\text{TlInS}_{2x}\text{Se}_{2(1-x)}$ ($0.25 \leq x \leq 1$) layered mixed crystals. <i>Crystal Research and Technology</i> , 2010, 45, 1141-1144.	1.3	6
121	Dynamical and passive characteristics of the Ag/TlGaSeS/Ag RF resonators. <i>Crystal Research and Technology</i> , 2012, 47, 615-619.	1.3	6
122	Thermoluminescence properties of $\text{Tl}_2\text{Ga}_2\text{S}_3\text{Se}$ layered single crystals. <i>Journal of Applied Physics</i> , 2013, 113, 193510.	2.5	6
123	Band gap and refractive index tunability in thallium based layered mixed crystals. <i>Journal of Applied Physics</i> , 2015, 118, 035701.	2.5	6
124	Composition dependence of lattice parameters and band gap energies of thallium based layered mixed crystals. <i>Indian Journal of Physics</i> , 2015, 89, 657-661.	1.8	6
125	Optical characterization of CuIn_5S_8 crystals by ellipsometry measurements. <i>Journal of Physics and Chemistry of Solids</i> , 2016, 91, 13-17.	4.0	6
126	Vibrational modes in $(\text{TlGaS}_2)_x(\text{TlGaSe}_2)_{1-x}$ mixed crystals by Raman measurements: compositional dependence of the mode frequencies and line-shapes. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 14330-14335.	2.2	6

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127	Structural and temperature-tuned bandgap characteristics of thermally evaporated \hat{I}^2 -In ₂ S ₃ thin films. Journal of Materials Science: Materials in Electronics, 2021, 32, 15851-15856.	2.2	6
128	Lattice parameters of TlGa _{1-x} In _x S ₂ and TlGa(S _{1-x} Se _x) ₂ layer mixed crystals. Crystal Research and Technology, 1994, 29, K51-K55.	1.3	5
129	Photoelectronic and electrical properties of InS crystals. Semiconductor Science and Technology, 2002, 17, 1288-1292.	2.0	5
130	Effect of crystal disorder on linewidth of the Raman modes in GaS _{1-x} Se _x layered mixed crystals. Crystal Research and Technology, 2003, 38, 962-967.	1.3	5
131	Trap levels in layered semiconductor TlInS _{1.9} Se _{0.1} . Physica Status Solidi A, 2003, 196, 422-428.	1.7	5
132	Dispersive optical constants of Tl ₂ InGaSe ₄ single crystals. Physica Scripta, 2007, 76, 249-252.	2.5	5
133	Temperature and excitation intensity tuned photoluminescence in Tl ₄ GaIn ₃ S ₈ layered single crystals. Crystal Research and Technology, 2008, 43, 514-521.	1.3	5
134	Trapping centers and their distribution in Tl ₂ InGaSe ₄ single crystals by thermally stimulated luminescence. Journal of Materials Science, 2014, 49, 2542-2547.	3.7	5
135	Influence of temperature on optical properties of electron-beam-evaporated ZnSe thin film. Physica Scripta, 2020, 95, 075804.	2.5	5
136	Temperature-tuned bandgap characteristics of Bi ₁₂ TiO ₂₀ sillenite single crystals. Journal of Materials Science: Materials in Electronics, 2021, 32, 1316-1322.	2.2	5
137	Raman Spectra of TlGa _x In _{1-x} S ₂ Layer Solid Solutions. Physica Status Solidi (B): Basic Research, 1980, 101, K121.	1.5	4
138	Critical currents in Bi-2223 tapes near T _c under magnetic field and \hat{I}^3 -irradiation. Superconductor Science and Technology, 2000, 13, 1625-1628.	3.5	4
139	Determination of carrier effective mass, impurity energy levels, and compensation ratio in Ga ₄ Se ₃ S layered crystals by Hall effect measurements. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1662-1665.	1.8	4
140	Absorption edge and optical constants of layered structured Tl ₂ Ga ₂ Se ₃ S single crystals. Physica Scripta, 2012, 85, 065701.	2.5	4
141	Dielectric and Photo-Dielectric Properties of TlGaSeS Crystals. Bulletin of Materials Science, 2014, 37, 505-509.	1.7	4
142	Determination of Trapping Parameters of Tl ₂ In ₂ S ₃ Se Layered Single Crystal by Thermoluminescence. Crystal Research and Technology, 2018, 53, 1700134.	1.3	4
143	Long-wavelength optical phonons in Ag ₃ B ₅ IIC ₉ VI single crystals. Crystal Research and Technology, 1990, 25, K53-K57.	1.3	3
144	Voltage-current characteristics of polycrystalline (Bi,Pb) ₂ Sr ₂ Ca ₂ Cu ₃ O ₁₀ superconductor at different magnetic fields and temperatures. Journal of Low Temperature Physics, 1996, 105, 957-962.	1.4	3

#	ARTICLE	IF	CITATIONS
145	Thermal lattice scattering mobility and carrier effective mass in intrinsic Tl ₂ InGaTe ₄ single crystals. Journal of Physics Condensed Matter, 2007, 19, 156206.	1.8	3
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